

Intel® Core™2 Duo Mobile Processor, Intel® Core™2 Solo Mobile Processor and Intel® Core™2 Extreme Mobile Processor on 45-nm Process

Datasheet

For platforms based on Mobile Intel® 4 Series Express Chipset Family March 2009

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Enhanced Intel SpeedStep® Technology for specified units of this processor are available. See the Processor Spec Finder at http:// processorfinder.intel.com or contact your Intel representative for more information.

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1 Introduction

The Intel® Core™2 Duo mobile processor, Intel® Core™2 Duo mobile processor lowvoltage (LV), ultra low-voltage (ULV) in small form factor (SFF) package and Intel® Core™2 Extreme mobile are high-performance, low-power mobile processor based on the Intel Core microarchitecture for Intel® Centrino® 2 processor technology.

This document contains electrical, mechanical and thermal specifications for the following processors:

- The Intel Core 2 Duo processors and Intel Core 2 Extreme processors support the Mobile Intel® 4 Series Express Chipset and Intel® ICH9M I/O controller.
	- Dual-core extreme edition (DC-XE)
	- Standard voltage (SV)
	- 25-W processor in standard package (Power Optimized Performance-POP)
- The Intel Core 2 Duo processor in SFF package supports the Mobile Intel® GS45 Express Chipset and Intel® ICH9M SFF I/O controller.

This document contains electrical, mechanical and thermal specifications for:

- Power Optimized Performance (POP) in SFF package
- Low-voltage (LV) Processor in SFF package
- Ultra-low voltage (ULV) dual-core (DC) and single-core (SC) Processors in SFF package

Notes: In this document

- 1. Intel Core 2 Duo processor, and the Intel Core 2 Extreme processor are referred to as the processor
- 2. Intel Core 2 Duo LV/ULV/POP processors are referred to as SFF processor
- 3. Mobile Intel 4 Series Express Chipset is referred as the GMCH.

Key features include:

- Dual-core processor for mobile with enhanced performance
- Supports Intel architecture with Intel® Wide Dynamic Execution
- Supports L1 cache-to-cache (C2C) transfer
- On-die, primary 32-KB instruction cache and 32-KB, write-back data cache in each core
- The processor in DC-XE, standard voltage (SV) and LV have an on-die, up to 6-MB second-level, shared cache with Advanced Transfer Cache architecture
- The processor in ULV single-core and dual-core have an on-die, up to 3-MB second-level, shared cache with Advanced Transfer Cache architecture
- Streaming SIMD extensions 2 (SSE2), streaming SIMD extensions 3 (SSE3), supplemental streaming SIMD extensions 3 (SSSE3) and SSE4.1 instruction sets
- The processor in DC-XE, SV and LV are offered at 1066-MHz, source-synchronous front side bus (FSB)
- The processor in ULV are offered at 800-MHz, source-synchronous FSB
- Advanced power management features including Enhanced Intel SpeedStep® Technology and dynamic FSB frequency switching

- Digital thermal sensor (DTS)
- Intel® 64 architecture
- Supports enhanced Intel® Virtualization Technology
- Enhanced Intel® Dynamic Acceleration Technology and Enhanced Multi-Threaded Thermal Management (EMTTM)
- Supports PSI2 functionality
- SV processor offered in Micro-FCPGA and Micro-FCBGA packaging technologies
- Processor in POP, LV and ULV are offered in Micro-FCBGA packaging technologies only
- Execute Disable Bit support for enhanced security
- Intel® Deep Power Down low-power state with P_LVL6 I/O support
- Support for Intel® Trusted Execution Technology
- Half ratio support (N/2) for core to bus ratio

1.1 Terminology

1.2 References

Material and concepts available in the following documents may be beneficial when reading this document.

NOTE: Contact your Intel representative for the latest revision of this document.

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2 Low Power Features

2.1 Clock Control and Low-Power States

The processor supports low-power states both at the individual core level and the package level for optimal power management.

A core may independently enter the C1/AutoHALT, C1/MWAIT, C2, C3, C4, Intel® Enhanced Deeper Sleep and Intel® Deep Power Down Technology low-power states. When both cores coincide in a common core low-power state, the central power management logic ensures the entire processor enters the respective package lowpower state by initiating a P_LVLx (P_LVL2, P_LVL3, P_LVL4, P_LVL5,P_LVL6) I/O read to the GMCH.

The processor implements two software interfaces for requesting low-power states: MWAIT instruction extensions with sub-state hints and P_LVLx reads to the ACPI P_BLK register block mapped in the processor's I/O address space. The P_LVLx I/O reads are converted to equivalent MWAIT C-state requests inside the processor and do not directly result in I/O reads on the processor FSB. The P_LVLx I/O Monitor address does not need to be set up before using the P_LVLx I/O read interface. The sub-state hints used for each P_LVLx read can be configured through the IA32_MISC_ENABLES model specific register (MSR).

If a core encounters a GMCH break event while STPCLK# is asserted, it asserts the PBE# output signal. Assertion of PBE# when STPCLK# is asserted indicates to system logic that individual cores should return to the C0 state and the processor should return to the Normal state.

[Figure 1](#page-11-0) shows the core low-power states and [Figure 2](#page-12-3) shows the package low-power states for the processor. [Table 1](#page-12-4) maps the core low-power states to package low-power states.

Figure 1. Core Low-Power States

Figure 2. Package Low-Power States

Table 1. Coordination of Core Low-Power States at the Package Level

NOTE:

1. AutoHALT or MWAIT/C1.

2.1.1 Core Low-Power State Descriptions

2.1.1.1 Core C0 State

This is the normal operating state for cores in the processor.

2.1.1.2 Core C1/AutoHALT Powerdown State

C1/AutoHALT is a low-power state entered when a core executes the HALT instruction. The processor core will transition to the C0 state upon occurrence of SMI#, INIT#, $LINT[1:0]$ (NMI, INTR), or FSB interrupt messages. RESET# will cause the processor to immediately initialize itself.

A System Management Interrupt (SMI) handler will return execution to either Normal state or the AutoHALT Powerdown state. See the *Intel® 64 and IA-32 Architectures Software Developer's Manuals, Volume 3A/3B: System Programmer's Guide* for more information.

The system can generate a STPCLK# while the processor is in the AutoHALT Powerdown state. When the system deasserts the STPCLK# interrupt, the processor will return execution to the HALT state.

While in AutoHALT Powerdown state, the dual-core processor will process bus snoops and snoops from the other core. The processor core will enter a snoopable sub-state (not shown in [Figure 1](#page-11-0)) to process the snoop and then return to the AutoHALT Powerdown state.

2.1.1.3 Core C1/MWAIT Powerdown State

C1/MWAIT is a low-power state entered when the processor core executes the MWAIT(C1) instruction. Processor behavior in the MWAIT state is identical to the AutoHALT state except that Monitor events can cause the processor core to return to the C0 state. See the *Intel® 64 and IA-32 Architectures Software Developer's Manuals, Volume 2A: Instruction Set Reference, A-M* and *Volume 2B: Instruction Set Reference, N-Z*, for more information.

2.1.1.4 Core C2 State

Individual cores of the dual-core processor can enter the C2 state by initiating a P_LVL2 I/O read to the P_BLK or an MWAIT(C2) instruction, but the processor will not issue a Stop-Grant Acknowledge special bus cycle unless the STPCLK# pin is also asserted.

While in the C2 state, the dual-core processor will process bus snoops and snoops from the other core. The processor core will enter a snoopable sub-state (not shown in [Figure 1\)](#page-11-0) to process the snoop and then return to the C2 state.

2.1.1.5 Core C3 State

Individual cores of the dual-core processor can enter the C3 state by initiating a P_LVL3 I/O read to the P_BLK or an MWAIT(C3) instruction. Before entering C3, the processor core flushes the contents of its L1 caches into the processor's L2 cache. Except for the caches, the processor core maintains all its architectural states in the C3 state. The Monitor remains armed if it is configured. All of the clocks in the processor core are stopped in the C3 state.

Because the core's caches are flushed the processor keeps the core in the C3 state when the processor detects a snoop on the FSB or when the other core of the dual-core processor accesses cacheable memory. The processor core will transition to the C0 state upon occurrence of a Monitor event, SMI#, INIT#, LINT[1:0] (NMI, INTR), or FSB interrupt message. RESET# will cause the processor core to immediately initialize itself.

2.1.1.6 Core C4 State

Individual cores of the dual-core processor can enter the C4 state by initiating a P_LVL4 or P_LVL5 I/O read to the P_BLK or an MWAIT(C4) instruction. The processor core behavior in the C4 state is nearly identical to the behavior in the C3 state. The only difference is that if both processor cores are in C4, the central power management logic will request that the entire processor enter the Deeper Sleep package low-power state (see [Section 2.1.2.6\)](#page-16-0).

To enable the package-level Intel Enhanced Deeper Sleep state, Dynamic Cache Sizing and Intel Enhanced Deeper Sleep state fields must be configured in the PMG_CST_CONFIG_CONTROL MSR. Refer to [Section 2.1.2.6](#page-16-0) for further details on Intel Enhanced Deeper Sleep state.

2.1.1.7 Core Deep Power Down Technology (Code Name C6) State

Deep Power Down Technology state is a new, power-saving state which is being implemented on the processor. In Deep Power Down Technology the processor saves its entire architectural state onto an on-die SRAM hence allowing it to lower its main core voltage to any value, even as low as 0-V.

When the core enters Deep Power Down Technology state, it saves the processor state that is relevant to the processor context in an on-die SRAM that resides on a separate power plane V_{CCP} (I/O power supply). This allows the main core Vcc to be lowered to any arbitrary voltage including 0-V. The on-die storage for saving the processor state is implemented as a per-core SRAM.

2.1.2 Package Low-power State Descriptions

2.1.2.1 Normal State

This is the normal operating state for the processor. The processor remains in the Normal state when at least one of its cores is in the C0, C1/AutoHALT, or C1/MWAIT state.

2.1.2.2 Stop-Grant State

When the STPCLK# pin is asserted, each core of the dual-core processor enters the Stop-Grant state within 20 bus clocks after the response phase of the processor-issued Stop-Grant Acknowledge special bus cycle. Processor cores that are already in the C2, C3, or C4 state remain in their current low-power state. When the STPCLK# pin is deasserted, each core returns to its previous core low-power state.

Since the AGTL+ signal pins receive power from the FSB, these pins should not be driven (allowing the level to return to V_{CCP}) for minimum power drawn by the termination resistors in this state. In addition, all other input pins on the FSB should be driven to the inactive state.

RESET# causes the processor to immediately initialize itself, but the processor will stay in Stop-Grant state. When RESET# is asserted by the system, the STPCLK#, SLP#, DPSLP#, and DPRSTP# pins must be deasserted prior to RESET# deassertion as per AC Specification T45. When re-entering the Stop-Grant state from the Sleep state, STPCLK# should be deasserted after the deassertion of SLP# as per AC Specification T75.

While in Stop-Grant state, the processor will service snoops and latch interrupts delivered on the FSB. The processor will latch SMI#, INIT# and LINT[1:0] interrupts and will service only one of each upon return to the Normal state.

The PBE# signal may be driven when the processor is in Stop-Grant state. PBE# will be asserted if there is any pending interrupt or Monitor event latched within the processor. Pending interrupts that are blocked by the EFLAGS.IF bit being clear will still cause assertion of PBE#. Assertion of PBE# indicates to system logic that the entire processor should return to the Normal state.

A transition to the Stop-Grant Snoop state occurs when the processor detects a snoop on the FSB (see [Section 2.1.2.3\)](#page-15-0). A transition to the Sleep state (see [Section 2.1.2.4\)](#page-15-1) occurs with the assertion of the SLP# signal.

2.1.2.3 Stop-Grant Snoop State

The processor responds to snoop or interrupt transactions on the FSB while in Stop-Grant state by entering the Stop-Grant Snoop state. The processor will stay in this state until the snoop on the FSB has been serviced (whether by the processor or another agent on the FSB) or the interrupt has been latched. The processor returns to the Stop-Grant state once the snoop has been serviced or the interrupt has been latched.

2.1.2.4 Sleep State

The Sleep state is a low-power state in which the processor maintains its context, maintains the phase-locked loop (PLL), and stops all internal clocks. The Sleep state is entered through assertion of the $SLP#$ signal while in the Stop-Grant state. The SLP# pin should only be asserted when the processor is in the Stop-Grant state. SLP# assertions while the processor is not in the Stop-Grant state is out of specification and may result in unapproved operation.

In the Sleep state, the processor is incapable of responding to snoop transactions or latching interrupt signals. No transitions or assertions of signals (with the exception of SLP#, DPSLP# or RESET#) are allowed on the FSB while the processor is in Sleep state. Snoop events that occur while in Sleep state or during a transition into or out of Sleep state will cause unpredictable behavior. Any transition on an input signal before the processor has returned to the Stop-Grant state will result in unpredictable behavior.

If RESET# is driven active while the processor is in the Sleep state, and held active as specified in the RESET# pin specification, then the processor will reset itself, ignoring the transition through the Stop-Grant state. If RESET# is driven active while the processor is in the Sleep state, the SLP# and STPCLK# signals should be deasserted immediately after RESET# is asserted to ensure the processor correctly executes the Reset sequence.

While in the Sleep state, the processor is capable of entering an even lower power state, the Deep Sleep state, by asserting the DPSLP# pin (See [Section 2.1.2.5](#page-15-2)). While the processor is in the Sleep state, the SLP# pin must be deasserted if another asynchronous FSB event needs to occur.

2.1.2.5 Deep Sleep State

The Deep Sleep state is entered through assertion of the DPSLP# pin while in the Sleep state. BCLK may be stopped during the Deep Sleep state for additional platform-level power savings. BCLK stop/restart timings on appropriate GMCH-based platforms with the CK505 clock chip are as follows:

- **Deep Sleep entry:** the system clock chip may stop/tristate BCLK within 2 BCLKs of DPSLP# assertion. It is permissible to leave BCLK running during Deep Sleep.
- **Deep Sleep exit:** the system clock chip must drive BCLK to differential DC levels within 2-3 ns of DPSLP# deassertion and start toggling BCLK within 10 BCLK periods.

To re-enter the Sleep state, the DPSLP# pin must be deasserted. BCLK can be restarted after DPSLP# deassertion as described above. A period of 15 microseconds (to allow for PLL stabilization) must occur before the processor can be considered to be in the Sleep state. Once in the Sleep state, the SLP# pin must be deasserted to re-enter the Stop-Grant state.

While in Deep Sleep state, the processor is incapable of responding to snoop transactions or latching interrupt signals. No transitions of signals are allowed on the FSB while the processor is in Deep Sleep state. When the processor is in Deep Sleep

state, it will not respond to interrupts or snoop transactions. Any transition on an input signal before the processor has returned to Stop-Grant state will result in unpredictable behavior.

2.1.2.6 Deeper Sleep State

The Deeper Sleep state is similar to the Deep Sleep state but further reduces core voltage levels. One of the potential lower core voltage levels is achieved by entering the base Deeper Sleep state. The Deeper Sleep state is entered through assertion of the DPRSTP# pin while in the Deep Sleep state. The following lower core voltage level is achieved by entering the Intel Enhanced Deeper Sleep state which is a sub-state of Deeper Sleep state. Intel Enhanced Deeper Sleep state is entered through assertion of the DPRSTP# pin while in the Deep Sleep only when the L2 cache has been completely shut down. Refer to Section 2.1.2.6.1 and [Section 2.1.2.6.3](#page-17-0) for further details on reducing the L2 cache and entering Intel Enhanced Deeper Sleep state.

In response to entering Deeper Sleep, the processor drives the VID code corresponding to the Deeper Sleep core voltage on the VID[6:0] pins.

Exit from Deeper Sleep or Intel Enhanced Deeper Sleep state is initiated by DPRSTP# deassertion when either core requests a core state other than C4 or either core requests a processor performance state other than the lowest operating point.

2.1.2.6.1 Intel® Enhanced Deeper Sleep State

Intel Enhanced Deeper Sleep state is a sub-state of Deeper Sleep that extends powersaving capabilities by allowing the processor to further reduce core voltage once the L2 cache has been reduced to zero ways and completely shut down. The following events occur when the processor enters Intel Enhanced Deeper Sleep state:

- The last core entering C4 issues a P_LVL4 or P_LVL5 I/O read or an MWAIT(C4) instruction and then progressively reduces the L2 cache to zero
- Once the L2 cache has been reduced to zero, the processor triggers a special chipset sequence to notify the chipset to redirect all FSB traffic, except APIC messages, to memory. The snoops are replied as misses by the chipset and are directed to main memory instead of the L2 cache. This allows for higher residency of the processor's Intel Enhanced Deeper Sleep state.
- The processor drives the VID code corresponding to the Intel Enhanced Deeper Sleep state core voltage on the VID[6:0] pins.

2.1.2.6.2 Deep Power Down State Technology (Code Named C6) State

When both cores have entered the CC6 state and the L2 cache has been shrunk down to zero ways, the processor will enter the Deep Power Down Technology state. To do so both cores save their architectural states in the on-die SRAM that resides in the V_{CCP} domain. At this point, the core V_{CC} will be dropped to the lowest core voltage closer to 0-V. The processor is now in an extremely low-power state.

In Intel Deep Power Down Technology state, the processor does not need to be snooped as all the caches are flushed before entering this state.

2.1.2.6.3 Dynamic Cache Sizing

Dynamic Cache Sizing allows the processor to flush and disable a programmable number of L2 cache ways upon each Deeper Sleep entry under the following conditions:

- The second core is already in C4 and Intel Enhanced Deeper Sleep state or Deep Power Down Technology state (C6) is enabled (as specified in [Section 2.1.1.6\)](#page-13-3).
- The C0 timer that tracks continuous residency in the Normal package state has not expired. This timer is cleared during the first entry into Deeper Sleep to allow consecutive Deeper Sleep entries to shrink the L2 cache as needed.
- The FSB speed to processor core speed ratio is below the predefined L2 shrink threshold.

The number of L2 cache ways disabled upon each Deeper Sleep entry is configured in the BBL_CR_CTL3 MSR. The C0 timer is referenced through the CLOCK_CORE_CST_CONTROL_STT MSR. The shrink threshold under which the L2 cache size is reduced is configured in the PMG_CST_CONFIG_CONTROL MSR. If the FSB speed to processor core speed ratio is above the predefined L2 shrink threshold, then L2 cache expansion will be requested. If the ratio is zero, then the ratio will not be taken into account for Dynamic Cache Sizing decisions.

Upon STPCLK# deassertion, the first core exiting Intel Enhanced Deeper Sleep state or Deep Power Down Technology state will expand the L2 cache to two ways and invalidate previously disabled cache ways. If the L2 cache reduction conditions stated above still exist when the last core returns to C4 and the package enters Intel Enhanced Deeper Sleep state or Deep Power Down Technology state (C6), then the L2 will be shrunk to zero again. If a core requests a processor performance state resulting in a higher ratio than the predefined L2 shrink threshold, the C0 timer expires, or the second core (not the one currently entering the interrupt routine) requests the C1, C2, or C3 states, then the whole L2 will be expanded upon the next interrupt event.

In addition, the processor supports Full Shrink on L2 cache. When the MWAIT Deep Power Down Technology state instruction is executed with a hint=0x2 in ECX[3:0], the micro code will shrink all the active ways of the L2 cache in one step. This ensures that the package enters Deep Power Down Technology immediately when both cores are in CC6 instead of iterating till the cache is reduced to zero. The operating system (OS) is expected to use this hint when it wants to enter the lowest power state and can tolerate the longer entry latency.

L2 cache shrink prevention may be enabled as needed on occasion through an MWAIT(C4) sub-state field. If shrink prevention is enabled, the processor does not enter Intel Enhanced Deeper Sleep state or Intel Deep Power Down state since the L2 cache remains valid and in full size.

2.2 Enhanced Intel SpeedStep® Technology

The processor features Enhanced Intel SpeedStep Technology. Following are the key features of Enhanced Intel SpeedStep Technology:

- Multiple voltage and frequency operating points provide optimal performance at the lowest power.
- Voltage and frequency selection is software-controlled by writing to processor MSRs:
	- If the target frequency is higher than the current frequency, V_{CC} is ramped up in steps by placing new values on the VID pins, and the PLL then locks to the new frequency.
	- If the target frequency is lower than the current frequency, the PLL locks to the new frequency and the V_{CC} is changed through the VID pin mechanism.
	- Software transitions are accepted at any time. If a previous transition is in progress, the new transition is deferred until the previous transition completes.
- The processor controls voltage ramp rates internally to ensure glitch-free transitions.
- Low transition latency and large number of transitions possible per second:
	- $-$ Processor core (including L2 cache) is unavailable for up to 10 μ s during the frequency transition.
	- The bus protocol (BNR# mechanism) is used to block snooping.
- Improved Intel® Thermal Monitor mode:
	- When the on-die thermal sensor indicates that the die temperature is too high the processor can automatically perform a transition to a lower frequency and voltage specified in a software-programmable MSR.
	- The processor waits for a fixed time period. If the die temperature is down to acceptable levels, an up-transition to the previous frequency and voltage point occurs.
	- An interrupt is generated for the up and down Intel Thermal Monitor transitions enabling better system-level thermal management.
- Enhanced thermal management features:
	- Digital Thermal Sensor and Out of Specification detection.
	- Intel Thermal Monitor 1 (TM1) in addition to Intel Thermal Monitor 2 (TM2) in case of unsuccessful TM2 transition.
	- Dual-core thermal management synchronization.

Each core in the dual-core processor implements an independent MSR for controlling Enhanced Intel SpeedStep Technology, but both cores must operate at the same frequency and voltage. The processor has performance state coordination logic to resolve frequency and voltage requests from the two cores into a single frequency and voltage request for the package as a whole. If both cores request the same frequency and voltage, then the processor will transition to the requested common frequency and voltage. If the two cores have different frequency and voltage requests, then the processor will take the highest of the two frequencies and voltages as the resolved request and transition to that frequency and voltage.

The processor also supports Dynamic FSB Frequency Switching and Intel Dynamic Acceleration Technology mode on select SKUs. The operating system can take advantage of these features and request a lower operating point called SuperLFM (due to Dynamic FSB Frequency Switching) and a higher operating point Intel Dynamic Acceleration Technology mode.

2.3 Extended Low-Power States

Extended low-power states (CXE) optimize for power by forcibly reducing the performance state of the processor when it enters a package low-power state. Instead of directly transitioning into the package low-power state, the enhanced package lowpower state first reduces the performance state of the processor by performing an Enhanced Intel SpeedStep Technology transition down to the lowest operating point. Upon receiving a break event from the package low-power state, control will be returned to software while an Enhanced Intel SpeedStep Technology transition up to the initial operating point occurs. The advantage of this feature is that it significantly reduces leakage while in the Stop-Grant and Deeper Sleep states.

Deep Power Down Technology is always enabled in the extended low power state as described above.

Note: Long-term reliability cannot be assured unless all the Extended Low Power States are enabled.

> The processor implements two software interfaces for requesting enhanced package low-power states: MWAIT instruction extensions with sub-state hints and via BIOS by configuring IA32_MISC_ENABLES MSR bits to automatically promote package lowpower states to enhanced package low-power states.

- *Caution:* **Extended Stop-Grant and Enhanced Deeper Sleep must be enabled via the BIOS for the processor to remain within specification.** As processor technology changes, enabling the extended low power states becomes increasingly crucial when building computer systems. Maintaining the proper BIOS configuration is key to reliable, long-term system operation. Not complying to this guideline may affect the long-term reliability of the processor.
- *Caution:* **Enhanced Intel SpeedStep Technology transitions are multistep processes that require clocked control.** These transitions cannot occur when the processor is in the Sleep or Deep Sleep package low-power states since processor clocks are not active in these states. Extended Deeper Sleep is an exception to this rule when the Hard C4E configuration is enabled in the IA32_MISC_ENABLES MSR. This Extended Deeper Sleep state configuration will lower core voltage to the Deeper Sleep level while in Deeper Sleep and, upon exit, will automatically transition to the lowest operating voltage and frequency to reduce snoop service latency. The transition to the lowest operating point or back to the original software-requested point may not be instantaneous. Furthermore, upon very frequent transitions between active and idle states, the transitions may lag behind the idle state entry resulting in the processor either executing for a longer time at the lowest operating point or running idle at a high operating point. Observations and analyses show this behavior should not significantly impact total power savings or performance score while providing power benefits in most other cases.

2.4 FSB Low Power Enhancements

The processor incorporates FSB low power enhancements:

- Dynamic FSB Power Down
- BPRI# control for address and control input buffers
- Dynamic Bus Parking
- Dynamic On-Die Termination disabling
- Low V_{CCP} (I/O termination voltage)
- Dynamic FSB frequency switching

The processor incorporates the $DPWR#$ signal that controls the data bus input buffers on the processor. The DPWR# signal disables the buffers when not used and activates them only when data bus activity occurs, resulting in significant power savings with no performance impact. BPRI# control also allows the processor address and control input buffers to be turned off when the BPRI# signal is inactive. Dynamic Bus Parking allows a reciprocal power reduction in GMCH address and control input buffers when the processor deasserts its BR0# pin. The On-Die Termination on the processor FSB buffers is disabled when the signals are driven low, resulting in additional power savings. The low I/O termination voltage is on a dedicated voltage plane independent of the core voltage, enabling low I/O switching power at all times.

2.4.1 Dynamic FSB Frequency Switching

Dynamic FSB frequency switching effectively reduces the internal bus clock frequency in half to further decrease the minimum processor operating frequency from the Enhanced Intel SpeedStep Technology performance states and achieve the Super Low Frequency Mode (Super LFM). This feature is supported at FSB frequencies of 1066 MHz, 800 MHz and 667 MHz and does not entail a change in the external bus signal (BCLK) frequency. Instead, both the processor and GMCH internally lower their BCLK reference frequency to 50% of the externally visible frequency. Both the processor and GMCH maintain a virtual BCLK signal (VBCLK) that is aligned to the external BCLK but at half the frequency. After a downward shift, it would appear externally as if the bus is running with a 133-MHz base clock in all aspects, except that the actual external BCLK remains at 266 MHz. See [Figure 3](#page-21-1) for details. The transition into Super LFM, a "down-shift," is done following a handshake between the processor and GMCH. A similar handshake is used to indicate an "up-shift," a change back to normal operating mode. Please ensure this feature is enabled and supported in the BIOS.

Figure 3. Dynamic FSB Frequency Switching Protocol

NOTES:

- 1. All common clock signals will be active for two BCLKs instead of one (e.g., $ADS#$, $HIT#$).
- 2. The double-pumped signal strobes will have only one transition per BCLK when active, instead of two.
- 3. The quad-pumped signal strobes will have only two transitions per BCLK when active, instead of four.
- 4. Same setup and hold times apply, but relative to every second rising BCLK.
- 5. Following a RESET#, the bus will be in the legacy full-frequency mode.
- 6. There will not be a down-shift right after RESET# deassertion.
- 7. There is no backing out of a transition into or out of half-frequency mode. Once the sequence starts it must be completed.

2.4.2 Enhanced Intel® Dynamic Acceleration Technology

The processor supports Intel Dynamic Acceleration Technology mode. The Intel Dynamic Acceleration Technology feature allows one core of the processor to operate at a higher frequency point when the other core is inactive and the operating system requests increased performance. This higher frequency is called the opportunistic frequency and the maximum rated operating frequency is the ensured frequency.

The processor includes a hysteresis mechanism that improves overall Intel Dynamic Acceleration Technology performance by decreasing unnecessary transitions of the cores in and out of Intel Dynamic Acceleration Technology mode. Normally, the processor would exit Intel Dynamic Acceleration Technology as soon as two cores are active. This can become an issue if the idle core is frequently awakened for a short periods (i.e., high timer tick rates). The hysteresis mechanism allows two cores to be active for a limited time before it transitions out of Intel Dynamic Acceleration Technology mode.

Intel Dynamic Acceleration Technology mode enabling requires:

- Exposure, via BIOS, of the opportunistic frequency as the highest ACPI P state
- Enhanced Multi-Threaded Thermal Management (EMTTM)
- Intel Dynamic Acceleration Technology mode and EMTTM MSR configuration via BIOS.

When in Intel Dynamic Acceleration Technology mode, it is possible for both cores to be active under certain internal conditions. In such a scenario the processor may draw a Instantaneous current $(I_{CC_CORE_INST})$ for a short duration of t_{INST} ; however, the average I_{CC} current will be lesser than or equal to I_{CCDES} current specification. Please refer to the Processor DC Specifications section for more details.

2.5 VID-x

The processor implements the VID-x feature for improved control of core voltage levels when the processor enters a reduced power consumption state. VID-x applies only when the processor is in the Intel Dynamic Acceleration Technology performance state and one or more cores are in low-power state (i.e., CC3/CC4/CC6). VID-x provides the ability for the processor to request core voltage level reductions greater than one VID tick. The amount of VID tick reduction is fixed and only occurs while the processor is in Intel Dynamic Acceleration Technology mode. This improved voltage regulator efficiency during periods of reduced power consumption allows for leakage current reduction which results in platform power savings and extended battery life.

When in Intel Dynamic Acceleration Technology mode, it is possible for both cores to be active under certain internal conditions. In such a scenario the processor may draw a Instantaneous current $(I_{\text{CC_CORE_INST}})$ for a short duration of t_{INST} ; however, the average I_{CC} current will be lesser than or equal to I_{CCDES} current specification. Please refer to the Processor DC Specifications section for more details.

2.6 Processor Power Status Indicator (PSI-2) Signal

The processor incorporates the $PSI#$ signal that is asserted when the processor is in a reduced power consumption state. $PSI#$ can be used to improve intermediate and light load efficiency of the voltage regulator, resulting in platform power savings and extended battery life. The algorithm that the processor uses for determining when to assert PSI# is different from the algorithm used in previous mobile processors. PSI-2 functionality is expanded further to support three processor states:

- Both cores are in idle state
- Only one core active state
- Both cores are in active state

PSI-2 functionality improves overall voltage regulator efficiency over a wide power range based on the C-state and P-state of the two cores. The combined C-state and Pstate of both cores are used to dynamically predict processor power.

The real-time power prediction is compared against a set of predefined and configured values of **CHH** and **CHL**. **CHH** is indicative of the active C-state of both the cores and **CHL** is indicative that only one core is in active C-state and the other core is in low power core state. PSI-2# output is asserted upon crossing these thresholds indicating that the processor requires lower power. The voltage regulator will adapt its power output accordingly. Additionally the voltage regulator may switch to a single phase and/ or asynchronous mode when the processor is idle and fused leakage limit is less than or equal to the BIOS threshold value.

§

3 Electrical Specifications

3.1 Power and Ground Pins

For clean, on-chip power distribution, the processor will have a large number of V_{CC} (power) and V_{SS} (ground) inputs. All power pins must be connected to V_{CC} power planes while all V_{SS} pins must be connected to system ground planes. Use of multiple power and ground planes is recommended to reduce I*R drop. The processor V_{CC} pins must be supplied the voltage determined by the VID (Voltage ID) pins.

3.2 Decoupling Guidelines

Due to its large number of transistors and high internal clock speeds, the processor is capable of generating large average current swings between low and full power states. This may cause voltages on power planes to sag below their minimum values if bulk decoupling is not adequate. Larger bulk storage, such as electrolytic capacitors, supply current during longer lasting changes in current demand by the component, such as coming out of an idle condition. Similarly, they act as a storage well for current when entering an idle condition from a running condition. Care must be taken in the board design to ensure that the voltage provided to the processor remains within the specifications listed in the tables in [Section 3.10](#page-31-0). Failure to do so can result in timing violations or reduced lifetime of the component.

3.2.1 V_{CC} Decoupling

 V_{CC} regulator solutions need to provide bulk capacitance with a low Effective Series Resistance (ESR) and keep a low interconnect resistance from the regulator to the socket. Bulk decoupling for the large current swings when the part is powering on, or entering/exiting low-power states, should be provided by the voltage regulator solution depending on the specific system design.

3.2.2 FSB AGTL+ Decoupling

The processors integrate signal termination on the die as well as incorporate high frequency decoupling capacitance on the processor package. Decoupling must also be provided by the system motherboard for proper AGTL+ bus operation.

3.2.3 FSB Clock (BCLK[1:0]) and Processor Clocking

BCLK[1:0] directly controls the FSB interface speed as well as the core frequency of the processor. As in previous-generation processors, the processor core frequency is a multiple of the BCLK $[1:0]$ frequency. The processor bus ratio multiplier will be set at its default ratio at manufacturing. The processor uses a differential clocking implementation.

3.3 Voltage Identification and Power Sequencing

The processor uses seven voltage identification pins,VID[6:0], to support automatic selection of power supply voltages. The VID pins for the processor are CMOS outputs driven by the processor VID circuitry. [Table 2](#page-25-1) specifies the voltage level corresponding to the state of VID[6:0]. A 1 in the table refers to a high-voltage level and a 0 refers to a low-voltage level.

Table 2. Voltage Identification Definition (Sheet 1 of 3)

Table 2. Voltage Identification Definition (Sheet 2 of 3)

Table 2. Voltage Identification Definition (Sheet 3 of 3)

3.4 Catastrophic Thermal Protection

The processor supports the THERMTRIP# signal for catastrophic thermal protection. An external thermal sensor should also be used to protect the processor and the system against excessive temperatures. Even with the activation of THERMTRIP#, which halts all processor internal clocks and activity, leakage current can be high enough that the processor cannot be protected in all conditions without the removal of power to the processor. If the external thermal sensor detects a catastrophic processor temperature of approximately 125°C (maximum), or if the THERMTRIP# signal is asserted, the V_{CC} supply to the processor must be turned off within 500 ms to prevent permanent silicon damage due to thermal runaway of the processor. THERMTRIP# functionality is not ensured if the PWRGOOD signal is not asserted, and during Deep Power Down Technology State (C6).

3.5 Reserved and Unused Pins

All RESERVED (RSVD) pins must remain unconnected. Connection of these pins to V_{CC} , $V_{\rm sc}$, or to any other signal (including each other) can result in component malfunction or incompatibility with future processors. See [Section 4.2](#page-58-2) for a pin listing of the processor and the location of all RSVD pins.

For reliable operation, always connect unused inputs or bidirectional signals to an appropriate signal level. Unused active low AGTL+ inputs may be left as no-connects if AGTL+ termination is provided on the processor silicon. Unused active high inputs should be connected through a resistor to ground (V_{SS}). Unused outputs can be left unconnected. The TEST1,TEST2,TEST3,TEST4,TEST5,TEST6,TEST7 pins are used for test purposes internally and can be left as "No Connects".

3.6 FSB Frequency Select Signals (BSEL[2:0])

The BSEL[2:0] signals are used to select the frequency of the processor input clock (BCLK[1:0]). These signals should be connected to the clock chip and the appropriate chipset on the platform. The BSEL encoding for BCLK[1:0] is shown in [Table 3](#page-28-3).

Table 3. BSEL[2:0] Encoding for BCLK Frequency

3.7 FSB Signal Groups

The FSB signals have been combined into groups by buffer type in the following sections. In this document, the term "AGTL+ Input" refers to the AGTL+ input group as well as the AGTL+ I/O group when receiving. Similarly, "AGTL+ Output" refers to the AGTL+ output group as well as the AGTL+ I/O group when driving.

With the implementation of a source-synchronous data bus, two sets of timing parameters are specified. One set is for common clock signals, which are dependent upon the rising edge of BCLK0 (ADS#, HIT#, HITM#, etc.), and the second set is for the source-synchronous signals which are relative to their respective strobe lines (data and address) as well as the rising edge of BCLK0. Asychronous signals are still present (A20M#, IGNNE#, etc.) and can become active at any time during the clock cycle. [Table 4](#page-29-1) identifies which signals are common clock, source synchronous, and asynchronous.

Table 4. FSB Pin Groups

NOTES:See next page

- 1. Refer to [Chapter 4](#page-50-3) for signal descriptions and termination requirements.
- 2. In processor systems where there is no debug port implemented on the system board, these signals are used to support a debug port interposer. In systems with the debug port implemented on the system board, these signals are no connects.
- 3. BPM[2:1]# and PRDY# are AGTL+ output-only signals.
- 4. PROCHOT# signal type is open drain output and CMOS input.
- 5. On-die termination differs from other AGTL+ signals.

3.8 CMOS Signals

CMOS input signals are shown in [Table 4.](#page-29-1) Legacy output FERR#, IERR# and other non-AGTL+ signals (THERMTRIP# and PROCHOT#) use Open Drain output buffers. These signals do not have setup or hold time specifications in relation to BCLK[1:0]. However, all of the CMOS signals are required to be asserted for more than four BCLKs for the processor to recognize them. See [Section 3.10](#page-31-0) for the DC specifications for the CMOS signal groups.

3.9 Maximum Ratings

[Table 5](#page-30-2) specifies absolute maximum and minimum ratings only, which lie outside the functional limits of the processor. Only within specified operation limits, can functionality and long-term reliability be expected.

At conditions outside functional operation condition limits, but within absolute maximum and minimum ratings, neither functionality nor long-term reliability can be expected. If a device is returned to conditions within functional operation limits after having been subjected to conditions outside these limits, but within the absolute maximum and minimum ratings, the device may be functional, but with its lifetime degraded depending on exposure to conditions exceeding the functional operation condition limits.

At conditions exceeding absolute maximum and minimum ratings, neither functionality nor long-term reliability can be expected. Moreover, if a device is subjected to these conditions for any length of time then, when returned to conditions within the functional operating condition limits, it will either not function, or its reliability will be severely degraded.

Caution: Although the processor contains protective circuitry to resist damage from static electric discharge, precautions should always be taken to avoid high static voltages or electric fields.

Table 5. Processor Absolute Maximum Ratings

NOTES:

1. For functional operation, all processor electrical, signal quality, mechanical and thermal specifications must be satisfied.

- 2. Excessive overshoot or undershoot on any signal will likely result in permanent damage to the processor.
- 3. Storage temperature is applicable to storage conditions only. In this scenario, the processor must not receive a clock, and no lands can be connected to a voltage bias. Storage within these limits will not affect the long-term reliability of the device. For functional operation, please refer to the processor case temperature specifications.
- 4. This rating applies to the processor and does not include any tray or packaging.
- 5. Failure to adhere to this specification can affect the long-term reliability of the processor.
- 6. For Intel® Core™2 Duo mobile processors in 22x22 mm package.

3.10 Processor DC Specifications

The processor DC specifications in this section are defined at the processor core (pads) unless noted otherwise.

The tables list the DC specifications for the processor and are valid only while meeting specifications for junction temperature, clock frequency, and input voltages. The Highest Frequency Mode (HFM) and Lowest Frequency Mode (LFM) refer to the highest and lowest core operating frequencies supported on the processor. Active mode load line specifications apply in all states except in the Deep Sleep and Deeper Sleep states. $V_{\text{CC,BOOT}}$ is the default voltage driven by the voltage regulator at power up in order to set the VID values. Unless specified otherwise, all specifications for the processor are at T_1 = 105 °C. Read all notes associated with each parameter.

Table 6. Voltage and Current Specifications for the Dual-Core, Extreme Edition Processors (Sheet 1 of 2)

Table 6. Voltage and Current Specifications for the Dual-Core, Extreme Edition Processors (Sheet 2 of 2)

NOTES:

- 1. Each processor is programmed with a maximum valid voltage identification value (VID), which is set at manufacturing and cannot be altered. Individual maximum VID values are calibrated during manufacturing such that two processors at the same frequency may have different settings within the VID range. Note that this differs from the VID employed by the processor during a power management event (Intel Thermal Monitor 2, Enhanced Intel SpeedStep Technology, or Enhanced Halt State).
- 2. The voltage specifications are assumed to be measured across V_{CC_SENSE} and V_{SS_SENSE} pins at socket with a 100-MHz bandwidth oscilloscope, 1.5-pF maximum probe capacitance, and 1-MΩ minimum impedance. The maximum length of ground wire on the probe should be less than 5 mm. Ensure external noise from the system is not coupled in the scope probe.
- 3. Specified at $105 °C$ T_J.
4. Specified at the nomina
- 4. Specified at the nominal V_{CC}
5. Measured at the bulk capacitors
- Measured at the bulk capacitors on the motherboard.
- 6. $V_{CC,BOOT}$ tolerance shown in [Figure 4](#page-42-0) and [Figure 5](#page-43-0).
7. Based on simulations and averaged over the duration
- Based on simulations and averaged over the duration of any change in current. Specified by design/ characterization at nominal V_{CC} . Not 100% tested.
- 8. This is a power-up peak current specification, which is applicable when V_{CC} is high and V_{CC_CORE} is low.
9. This is a steady-state I_{CC} current specification, which is applicable when both V_{CC} and V_{CC} cope
- 9. This is a steady-state I_{CC} current specification, which is applicable when both V_{CCP} and V_{CC_CORE} are high.
- 10. The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than or equal to 300 mV.
- 11. The I_{CCDES} (max) specification of 60 A is for Intel® Core[™]2 Extreme processors only.

NOTES:See next page.

- 1. Each processor is programmed with a maximum valid voltage identification value (VID), which is set at manufacturing and cannot be altered. Individual maximum VID values are calibrated during manufacturing such that two processors at the same frequency may have different settings within the VID range. Note that this differs from the VID employed by the processor during a power management event (Intel Thermal Monitor 2, Enhanced Intel SpeedStep Technology, or Enhanced Halt State).
- 2. The voltage specifications are assumed to be measured across V_{CC_SENSE} and V_{SS_SENSE} pins at socket with a 100-MHz bandwidth oscilloscope, 1.5-pF maximum probe capacitance, and 1-MΩ minimum impedance. The maximum length of ground wire on the probe should be less than 5 mm. Ensure external noise from the system is not coupled in the scope probe.
- 3. Specified at $105 °C$ T_J.
4. Specified at the nomina
- 4. Specified at the nominal V_{CC} .
5. Measured at the bulk capacite
- Measured at the bulk capacitors on the motherboard.
- 6. $V_{CC,BOOT}$ tolerance shown in [Figure 7](#page-45-0) and [Figure 8](#page-46-0).
7. Based on simulations and averaged over the duration
- Based on simulations and averaged over the duration of any change in current. Specified by design/ characterization at nominal V_{CC} . Not 100% tested.
-
- 8. This is a power-up peak current specification that is applicable when V_{CC} is high and V_{CC_CORE} is low.
9. This is a steady-state I_{CC} current specification that is applicable when both V_{CC} and V_{CC_CORE} are hig 9. This is a steady-state I_{CC}current specification that is applicable when both V_{CCP} and V_{CC} core are high.
10. Processor I_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than I_{CC} in HFM
- 10. Processor I_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than I_{CC} in HFM
11. The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than
- The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than or equal to 300 mV.
- 12. Instantaneous current I_{CC} CORE INST of 57 A has to be sustained for short time (t_{INST}) of 35 µs. Average current will be less than maximum specified I_{CCDES} . VR OCP threshold should be high enough to support current levels described herein.

Table 8. Voltage and Current Specifications for the Dual-Core, Low-Power Standard-Voltage Processors (25 W) in Standard Package

Table 8. Voltage and Current Specifications for the Dual-Core, Low-Power Standard-Voltage Processors (25 W) in Standard Package

NOTES:.

- 1. Each processor is programmed with a maximum valid voltage identification value (VID), which is set at manufacturing and cannot be altered. Individual maximum VID values are calibrated during manufacturing such that two processors at the same frequency may have different settings within the VID range. Note that this differs from the VID employed by the processor during a power management event (Intel Thermal Monitor 2, Enhanced Intel SpeedStep Technology, or Enhanced Halt State).
- 2. The voltage specifications are assumed to be measured across V_{CC_SENSE} and V_{SS_SENSE} pins at socket with a 100-MHz bandwidth oscilloscope, 1.5-pF maximum probe capacitance, and 1-MΩ minimum impedance. The maximum length of ground wire on the probe should be less than 5 mm. Ensure external noise from the system is not coupled in the scope probe.
- 3. Specified at $105 °C$ T_J.
4. Specified at the nomina
- 4. Specified at the nominal V_{CC} .
5. Measured at the bulk capacite
- Measured at the bulk capacitors on the motherboard.
- 6. $V_{CC,BOOT}$ tolerance shown in [Figure 4](#page-42-0) and [Figure 5](#page-43-0).
7. Based on simulations and averaged over the duration
- Based on simulations and averaged over the duration of any change in current. Specified by design/ characterization at nominal V_{CC} . Not 100% tested.
- 8. This is a power-up peak current specification that is applicable when V_{CC} is high and V_{CC_CORE} is low.
9. This is a steady-state Lecurrent specification that is applicable when both Vecp and Vec copp are high
- 9. This is a steady-state I_{CC}current specification that is applicable when both V_{CCP} and V_{CC} core are high.
10. Processor I_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than I_{CC} in HFM
- 10. Processor I_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than I_{CC} in HFM
11. The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than
- The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than or equal to 300 mV.
- 12. Instantaneous current $I_{CC_CORE_INST}$ of 49 A has to be sustained for short time (t_{INST}) of 35 µs. Average current will be less than maximum specified I_{CCDES}. VR OCP threshold should be high enough to support current levels described herein.

NOTES:

1. Each processor is programmed with a maximum valid voltage identification value (VID), which is set at manufacturing and cannot be altered. Individual maximum VID values are calibrated during manufacturing such that two processors at the same frequency may have different settings within the VID range. Note

that this differs from the VID employed by the processor during a power management event (Intel Thermal Monitor 2, Enhanced Intel SpeedStep Technology, or Enhanced Halt State).

- 2. The voltage specifications are assumed to be measured across V_{CC_SENSE} and V_{SS_SENSE} pins at socket with a 100-MHz bandwidth oscilloscope, 1.5-pF maximum probe capacitance, and 1-MΩ minimum impedance. The maximum length of ground wire on the probe should be less than 5 mm. Ensure external noise from the system is not coupled in the scope probe.
- 3. Specified at 105 °C T_1 .
- 4. Specified at the nominal V_{CC} .
5. Measured at the bulk capacitors
- Measured at the bulk capacitors on the motherboard.
- 6. $V_{CC,BOOT}$ tolerance shown in [Figure 7](#page-45-0) and [Figure 8](#page-46-0).
7. Based on simulations and averaged over the duration
- Based on simulations and averaged over the duration of any change in current. Specified by design/ characterization at nominal V_{CC} . Not 100% tested.
- 8. This is a power-up peak current specification that is applicable when V_{CC} is high and V_{CC_CORE} is low.
9. This is a steady-state I_{CC} current specification that is applicable when both V_{CC} and V_{CC} cope are
- 9. This is a steady-state I_{CC} current specification that is applicable when both V_{CCP} and V_{CC}_coRE are high.
10. Processor I_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than I_{CC} in HF
- 10. Processor I_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than I_{CC} in HFM 11. The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than
- The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than or equal to 300 mV.
- 12. Instantaneous current I_{CC} CORE INST of 44 A has to be sustained for short time (t_{INST}) of 35 µs. Average current will be less than maximum specified I_{CCDES} . VR OCP threshold should be high enough to support current levels described herein.

Table 10. Voltage and Current Specifications for the Dual-Core, Low-Voltage SFF Processor

Table 10. Voltage and Current Specifications for the Dual-Core, Low-Voltage SFF Processor

- 1. Each processor is programmed with a maximum valid voltage identification value (VID), which is set at manufacturing and cannot be altered. Individual maximum VID values are calibrated during manufacturing such that two processors at the same frequency may have different settings within the VID range. Note that this differs from the VID employed by the processor during a power management event (Intel Thermal Monitor 2, Enhanced Intel SpeedStep Technology, or Enhanced Halt State).
- 2. The voltage specifications are assumed to be measured across V_{CC_SENSE} and V_{SS_SENSE} pins at socket with a 100-MHz bandwidth oscilloscope, 1.5-pF maximum probe capacitance, and 1-MΩ minimum impedance. The maximum length of ground wire on the probe should be less than 5 mm. Ensure external noise from the system is not coupled in the scope probe.
- 3. Specified at $105 °C T_J$.
4. Specified at the nomina
- 4. Specified at the nominal V_{CC} .
5. Measured at the bulk capacitors
- Measured at the bulk capacitors on the motherboard.
- 6. $V_{CC,BOOT}$ tolerance shown in [Figure 7](#page-45-0) and [Figure 8](#page-46-0).
7. Based on simulations and averaged over the duration
- Based on simulations and averaged over the duration of any change in current. Specified by design/ characterization at nominal V_{CC} . Not 100% tested.
- 8. This is a power-up peak current specification that is applicable when V_{CC} is high and V_{CC_CORE} is low.
9. This is a steady-state L_{CC} current specification that is applicable when both V_{CC} and V_{CC} corr are h
- 9. This is a steady-state I_{CC} current specification that is applicable when both V_{CC} and V_{CC} core are high.
10. Processor Icc requirements in Intel Dynamic Acceleration Technology mode are lesser than Icc in HFM
- 10. Processor I_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than I_{CC} in HFM
11. The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than
- The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than or equal to 300 mV.
- 12. Instantaneous current I_{CC} CORE INST of 36 A has to be sustained for short time (t_{INST}) of 35 µs. Average current will be less than $\overline{\text{maximm}}$ specified I_{CCDES}. VR OCP threshold should be high enough to support current levels described herein.

Table 11. Voltage and Current Specifications for the Dual-Core, Ultra-Low-Voltage SFF Processor

NOTES:See next page.

- 1. Each processor is programmed with a maximum valid voltage identification value (VID), which is set at manufacturing and cannot be altered. Individual maximum VID values are calibrated during manufacturing such that two processors at the same frequency may have different settings within the VID range. Note that this differs from the VID employed by the processor during a power management event (Intel Thermal Monitor 2, Enhanced Intel SpeedStep Technology, or Enhanced Halt State).
- 2. The voltage specifications are assumed to be measured across V_{CC_SENSE} and V_{SS_SENSE} pins at socket with a 100-MHz bandwidth oscilloscope, 1.5-pF maximum probe capacitance, and 1-MΩ minimum impedance. The maximum length of ground wire on the probe should be less than 5 mm. Ensure external noise from the system is not coupled in the scope probe.
- 3. Specified at $105 °C$ T_J.
4. Specified at the nomina
- 4. Specified at the nominal V_{CC} .
5. Measured at the bulk capacite
- Measured at the bulk capacitors on the motherboard.
- 6. $V_{CC,BOOT}$ tolerance shown in [Figure 7](#page-45-0) and [Figure 8](#page-46-0).
7. Based on simulations and averaged over the duration
- Based on simulations and averaged over the duration of any change in current. Specified by design/ characterization at nominal V_{CC} . Not 100% tested.
-
- 8. This is a power-up peak current specification that is applicable when V_{CC} is high and V_{CC_CORE} is low.
9. This is a steady-state I_{CC} current specification that is applicable when both V_{CC} and V_{CC} core are 9. This is a steady-state I_{CC} current specification that is applicable when both V_{CCP} and V_{CC_CORE} are high.
- 10. Processor I_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than I_{CC} in HFM
- 11. The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than or equal to 300 mV.
- 12. Instantaneous current $I_{CC-CORE INST}$ of 24 A has to be sustained for short time (t_{INST}) of 35µs. Average current will be less than maximum specified I_{CCDES} . VR OCP threshold should be high enough to support current levels described herein.

Table 12. Voltage and Current Specifications for the Ultra-Low-Voltage, Single-Core (5.5 W) SFF Processor

Table 12. Voltage and Current Specifications for the Ultra-Low-Voltage, Single-Core (5.5 W) SFF Processor

- 1. Each processor is programmed with a maximum valid voltage identification value (VID), which is set at manufacturing and cannot be altered. Individual maximum VID values are calibrated during manufacturing such that two processors at the same frequency may have different settings within the VID range. Note that this differs from the VID employed by the processor during a power management event (Intel Thermal Monitor 2, Enhanced Intel SpeedStep Technology, or Enhanced Halt State).
- 2. The voltage specifications are assumed to be measured across $V_{CC-SENSE}$ and $V_{SS-SENSE}$ pins at socket with a 100-MHz bandwidth oscilloscope, 1.5-pF maximum probe capacitance, and 1-MΩ minimum impedance. The maximum length of ground wire on the probe should be less than 5 mm. Ensure external noise from the system is not coupled in the scope probe.
- 3. Specified at 100 °C T_1 .
4. Specified at the nomina
- 4. Specified at the nominal V_{CC} .
5. Measured at the bulk capacite
- Measured at the bulk capacitors on the motherboard.
- 6. $V_{CC,BOOT}$ tolerance shown in [Figure 4](#page-42-0) and [Figure 5](#page-43-0).
7. Based on simulations and averaged over the duration
- Based on simulations and averaged over the duration of any change in current. Specified by design/ characterization at nominal V_{CC} . Not 100% tested.
- 8. This is a power-up peak current specification that is applicable when V_{CC} is high and V_{CC_CORE} is low.
9. This is a steady-state Lee current specification that is applicable when both V_{CC} and V_{CC} core are big
- 9. This is a steady-state I_{CC} current specification that is applicable when both V_{CC} and V_{CC} core are high.
10. Processor L_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than L_{CC} in
- 10. Processor I_{CC} requirements in Intel Dynamic Acceleration Technology mode are lesser than I_{CC} in HFM 11. The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than
- The maximum delta between Intel Enhanced Deeper Sleep and LFM on the processor will be lesser than or equal to 300 mV.

Figure 4. Active V_{CC} and I_{CC} Loadline for Standard Voltage, Low-Power SV (25 W) and **Dual-Core, Extreme Edition Processors**

Figure 5. Deeper Sleep V_{CC} and I_{CC} Loadline for Standard-Voltage, Low-Power SV **(25 W) and Dual-Core Extreme Edition Processors**

NOTE: Deeper Sleep mode tolerance depends on VID value.

Figure 6. Deeper Sleep V_{CC} and I_{CC} Loadline for Low-Power Standard-Voltage **Processors**

- 1. Applies to low-power standard-voltage 22-mm (dual-core) processors.
- 2. Deeper Sleep mode tolerance depends on VID value.

Figure 7. Active VCC and ICC Loadline for Low-Voltage, Ultra-Low-Voltage and Power Optimized Performance Processor

- 1. Applies to Low-Voltage, Ultra-Low-Voltage and Power Optimised Performance processors in 22 mmx22 mm package.
- 2. Active mode tolerance depends on VID value

Figure 8. Deeper Sleep VCC and ICC Loadline for Low-Voltage, Ultra-Low-Voltage and Power Optimized Performance Processor

- 1. Applies to Low-Voltage, Ultra-Low-Voltage and Power Optimised Performance processors in 22 mmx22 mm package.
- 2. Deeper Sleep mode tolerance depends on VID value.

Table 13. AGTL+ Signal Group DC Specifications

- 1. Unless otherwise noted, all specifications in this table apply to all processor frequencies.
- 2. V_{II} is defined as the maximum voltage level at a receiving agent that will be interpreted as a logical low value.
- 3. V_{IH} is defined as the minimum voltage level at a receiving agent that will be interpreted as a logical high value.
- 4. V_{IH} and V_{OH} may experience excursions above V_{CCP} However, input signal drivers must comply with the signal quality specifications.
- 5. This is the pulldown driver resistance. Measured at $0.31*V_{CCP}$ R_{ON} (min) = $0.418*R_{TT}$, R_{ON} (typ) = $0.455*R$ _{TT},
	- R_{ON} (max) = 0.527*R_{TT}. R_{TT} typical value of 55 Ω is used for R_{ON} typ/min/max calculations.
- 6. GTLREF should be generated from V_{CCP} with a 1% tolerance resistor divider. The V_{CCP} referred to in these specifications is the instantaneous V_{CCP} .
- 7. R_{TT} is the on-die termination resistance measured at V_{OL} of the AGTL+ output driver. Measured at $0.31*V_{\text{CCP}}$ R_{TT} is connected to V_{CCP} on die. Refer to processor I/O buffer models for I/V characteristics.
- 8. Specified with on-die R_{TT} and R_{ON} turned off. Vin between 0 and V_{CCP}
9. Cpad includes die capacitance only. No package parasitics are included
- Cpad includes die capacitance only. No package parasitics are included.
- 10. This is the external resistor on the comp pins.
- 11. On-die termination resistance, measured at $0.33*V_{\text{CCP}}$
12. Applies to Signals A[35:3].
- Applies to Signals A[35:3].
- 13. Applies to Signals D[63:0].
- 14. Applies to Signals BPRI#, DEFER#, PREQ#, PREST#, RS[2:0]#, TRDY#, ADS#, BNR#, BPM[3:0], BR0#, $DSY#$, DRDY#, HIT#, HITM#, LOCK#, PRDY#, DPWR#, DSTB[1:0]#, DSTBP[3:0] and DSTBN[3:0]#.

Table 14. CMOS Signal Group DC Specifications

NOTES:

- 1. Unless otherwise noted, all specifications in this table apply to all processor frequencies.
- 2. The V_{CCP} referred to in these specifications refers to instantaneous V_{CCP}.
3. Measured at 0.1 *V_{CCP}
- 3. Measured at 0.1 $*V_{CCP}$
4. Measured at 0.9 $*V_{CCP}$
- 4. Measured at 0.9 *V_{CCP}.
5. For Vin between 0 V an
- 5. For Vin between 0 V and V_{CCP} . Measured when the driver is tristated.
6. Cpad1 includes die capacitance only for DPRSTP#, DPSLP#, PWRGOC
- 6. Cpad1 includes die capacitance only for DPRSTP#, DPSLP#, PWRGOOD. No package parasitics are included.
- 7. Cpad2 includes die capacitance for all other CMOS input signals. No package parasitics are included.

Table 15. Open Drain Signal Group DC Specifications

NOTES:

1. Unless otherwise noted, all specifications in this table apply to all processor frequencies.

2. Measured at 0.2 V.

3. V_{OH} is determined by value of the external pull-up resistor to V_{CCP}
4. For Vin between 0 V and V_{OH}.

4. For Vin between 0 V and V_{OH} .
5. Cpad includes die capacitance

5. Cpad includes die capacitance only. No package parasitics are included.

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4 Package Mechanical Specifications and Pin Information

4.1 Package Mechanical Specifications

The processor (XE and SV) is available in 478-pin Micro-FCPGA packages as well as 479-ball Micro-FCBGA packages. The package mechanical dimensions are shown in [Figure 9](#page-51-0) through [Figure 13.](#page-55-0)

The processor (POP, LV, ULV DC and ULV SC) is available 956-ball Micro-FCBGA packages. The package mechanical dimensions are shown in [Figure 14](#page-56-0) and [Figure 15](#page-57-0). The maximum outgoing co-planarity is 0.2 mm (8 mils) for SFF processors.

The mechanical package pressure specifications are in a direction normal to the surface of the processor. This protects the processor die from fracture risk due to uneven die pressure distribution under tilt, stack-up tolerances and other similar conditions. These specifications assume that a mechanical attach is designed specifically to load one type of processor.

A 15-lbf load limit should not be exceeded on BGA packages so as to not impact solder joint reliability after reflow. This load limit ensures that impact to the package solder joints due to transient bend, shock, or tensile loading is minimized. The 15-lbf metric should be used **in parallel** with the 689-kPa (100 psi) pressure limit as long as neither limits are exceeded. In some cases, designing to 15 lbf will exceed the pressure specification of 689 kPa (100 psi) and therefore should be reduced to ensure both limits are maintained.

Moreover, the processor package substrate should not be used as a mechanical reference or load-bearing surface for the thermal or mechanical solution.

Caution: The Micro-FCBGA package incorporates land-side capacitors. The land-side capacitors are electrically conductive so care should be taken to avoid contacting the capacitors with other electrically conductive materials on the motherboard. Doing so may short the capacitors and possibly damage the device or render it inactive.

Figure 9. 6-MB and 3-MB on 6-MB Die Micro-FCPGA Package Drawing (Sheet 1 of 2)

Figure 10. 3-MB die Micro-FCPGA Processor Package Drawing (Sheet 1 of 2)

Figure 11. 3-MB Die Micro-FCPGA Processor Package Drawing (Sheet 2 of 2)

Figure 12. 3-MB Die Micro-FCBGA Processor Package Drawing (Sheet 1 of 2)

Figure 13. 3-MB Die Micro-FCBGA Processor Package Drawing (Sheet 2 of 2)

Figure 14. Intel Core 2 Duo Mobile Processor (POP and LV) Die Micro-FCBGA Processor Package Drawing

4.2 Processor Pinout and Pin List

[Figure 16](#page-58-0) and [Figure 17](#page-59-0) show the processor (SV and XE) pinout as viewed from the top of the package. [Table 16](#page-60-0) provides the pin list, arranged numerically by pin number. [Figure 16](#page-58-0) through [Figure 18](#page-79-0) show the top view of the LV and ULV processor package. [Table 18](#page-83-0) lists the SFF processor ballout alphabetically by signal name. For signal descriptions, refer to [Section 4.3.](#page-92-0)

Figure 16. Processor Pinout (Top Package View, Left Side)

NOTES:

1. Keying option for Micro-FCPGA, A1 and B1 are de-populated.

2. Keying option for Micro-FCBGA, A1 is de-populated and B1 is VSS.

Figure 17. Processor Pinout (Top Package View, Right Side)

\blacksquare Datasheet 61

Datasheet 67

Table 17. Pin # Listing

Pin#	Pin Name	Signal Buffer Type	Directi on
W24	$D[43]$ #	Source Synch	Input/ Output
W ₂₅	$D[44]$ #	Source Synch	Input/ Output
W26	VSS	Power/Other	
Y1	COMP _[3]	Power/Other	Input/ Output
Y2	A[17]#	Source Synch	Input/ Output
Y3	VSS	Power/Other	
Y4	$A[29]$ #	Source Synch	Input/ Output
Y ₅	$A[22]$ #	Source Synch	Input/ Output
Y6	VSS	Power/Other	
Y21	VSS	Power/Other	
Y22	$D[32]$ #	Source Synch	Input/ Output
Y23	D[42]#	Source Synch	Input/ Output
Y24	VSS	Power/Other	
Y25	$D[40]$ #	Source Synch	Input/ Output
Y26	DSTBN[2] #	Source Synch	Input/ Output

Table 17. Pin # Listing

Figure 18. Intel Core 2 Duo Mobile Processor in SFF Package Top View Upper Left Side

Figure 19. Intel Core 2 Duo Mobile Processor in SFF Package Top View Upper Right Side

Figure 20. Intel Core 2 Duo Mobile Processor in SFF Package Top View Lower Left Side

Figure 21. Intel Core 2 Duo Mobile Processor in SFF Package Top View Lower Right Side

Signal

Ball

Signal

 $A[34]$ # | AP2 | | D[15]# | L43 | | D[51]# | AU41 A[35]# AR1 D[16]# P44 D[52]# AW41 ADS# | C7 || D[17]# | V40 || D[53]# | AR41 $ADSTB[0]$ # | M4 | | D[18]# | V44 | | D[54]# | BA37 $ADSTB[1]$ # | Y4 | | D[19]# | AB44 | | D[55]# | BB38

Table 18.Intel Core 2 Duo Mobile Processor in SFF Package Listing by Ball Name

Number Signal Name Ball

4.3 Alphabetical Signals Reference

Table 19. Signal Description (Sheet 1 of 8)

Table 19. Signal Description (Sheet 2 of 8)

Table 19. Signal Description (Sheet 3 of 8)

Table 19. Signal Description (Sheet 4 of 8)

Table 19. Signal Description (Sheet 5 of 8)

Table 19. Signal Description (Sheet 6 of 8)

Table 19. Signal Description (Sheet 7 of 8)

Table 19. Signal Description (Sheet 8 of 8)

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5 Thermal Specifications and Design Considerations

A complete thermal solution includes both component and system-level thermal management features. To allow for the optimal operation and long-term reliability of Intel processor-based systems, the system/processor thermal solution should be designed so the processor remains within the minimum and maximum junction temperature (T_1) specifications at the corresponding thermal design power (TDP) value listed in the tables below

Caution: Operating the processor outside these operating limits may result in permanent damage to the processor and potentially other components in the system.

Table 20. Power Specifications for the Dual-Core Extreme Edition Processor

- 1. The TDP specification should be used to design the processor thermal solution. The TDP is not the maximum theoretical power the processor can generate.
- 2. Not 100% tested. These power specifications are determined by characterization of the processor currents at higher temperatures and extrapolating the values for the temperature indicated.
- 3. As measured by the activation of the on-die Intel Thermal Monitor. The Intel Thermal Monitor's automatic mode is used to indicate that the maximum T_J has been reached.
- 4. The Intel Thermal Monitor automatic mode must be enabled for the processor to operate within specifications.
- 5. Processor TDP requirements in Intel Dynamic Acceleration Technology mode are lesser than TDP in HFM.
- 6. At Ti of 105 °C
- 7. At Tj of 50 \degree C
- 8. At Tj of 35° C

- 1. The TDP specification should be used to design the processor thermal solution. The TDP is not the maximum theoretical power the processor can generate.
- 2. Not 100% tested. These power specifications are determined by characterization of the processor currents at higher temperatures and extrapolating the values for the temperature indicated.
- 3. As measured by the activation of the on-die Intel Thermal Monitor. The Intel Thermal Monitor's automatic mode is used to indicate that the maximum T_1 has been reached.
- 4. The Intel Thermal Monitor automatic mode must be enabled for the processor to operate within specifications.
- 5. Processor TDP requirements in Intel Dynamic Acceleration Technology mode are lesser than TDP in HFM.
- 6. At Tj of $105\,^{\circ}$ C
- 7. At Tj of 50 $^{\circ}$ C
- 8. At Tj of 35 \degree C

Table 22. Power Specifications for the Dual-Core Low Power Standard Voltage Processors (25W) in Standard Package

- 1. The TDP specification should be used to design the processor thermal solution. The TDP is not the maximum theoretical power the processor can generate.
- 2. Not 100% tested. These power specifications are determined by characterization of the processor currents at higher temperatures and extrapolating the values for the temperature indicated.
- 3. As measured by the activation of the on-die Intel Thermal Monitor. The Intel Thermal Monitor's automatic mode is used to indicate that the maximum T_1 has been reached. Refer to Section 6.1 for more details.
- 4. The Intel Thermal Monitor automatic mode must be enabled for the processor to operate within specifications.
- 5. Processor TDP requirements in Intel Dynamic Acceleration Technology mode are lesser than TDP in HFM.
- 6. At Tj of $105\,^{\circ}\text{C}$
- 7. At Tj of 50 \degree C
- 8. At Tj of 35° C

Table 23. Power Specifications for the Dual-Core Power Optimized Performance (25 W) SFF Processors

- 1. The TDP specification should be used to design the processor thermal solution. The TDP is not the maximum theoretical power the processor can generate.
- 2. Not 100% tested. These power specifications are determined by characterization of the processor currents at higher temperatures and extrapolating the values for the temperature indicated.
- 3. As measured by the activation of the on-die Intel Thermal Monitor. The Intel Thermal Monitor's automatic mode is used to indicate that the maximum T_1 has been reached.
- 4. The Intel Thermal Monitor automatic mode must be enabled for the processor to operate within specifications.
- 5. Processor TDP requirements in Intel Dynamic Acceleration Technology mode are lesser than TDP in HFM.
- 6. At Ti of 105° C
- 7. At Tj of 50 °C
- 8. At \overline{I} of 35 °C

Table 24. Power Specifications fro the Dual-Core Low Voltage (LV) SFF Processors

- 1. The TDP specification should be used to design the processor thermal solution. The TDP is not the maximum theoretical power the processor can generate.
- 2. Not 100% tested. These power specifications are determined by characterization of the processor currents at higher temperatures and extrapolating the values for the temperature indicated.
- 3. As measured by the activation of the on-die Intel Thermal Monitor. The Intel Thermal Monitor's automatic mode is used to indicate that the maximum T_J has been reached.
- 4. The Intel Thermal Monitor automatic mode must be enabled for the processor to operate within specifications.
- 5. Processor TDP requirements in Intel Dynamic Acceleration Technology mode are lesser than TDP in HFM.
- 6. At Tj of 105 °C
- 7. At Tj of 50 °C
- 8. At Ti of 35 °C

Table 25. Power Specifications for the Dual-Core Ultra-Low-Voltage (ULV) Processors

- 1. The TDP specification should be used to design the processor thermal solution. The TDP is not the maximum theoretical power the processor can generate.
- 2. Not 100% tested. These power specifications are determined by characterization of the processor currents at higher temperatures and extrapolating the values for the temperature indicated.
- 3. As measured by the activation of the on-die Intel Thermal Monitor. The Intel Thermal Monitor's automatic mode is used to indicate that the maximum T_1 has been reached.
- 4. The Intel Thermal Monitor automatic mode must be enabled for the processor to operate within specifications.
- 5. Processor TDP requirements in Intel Dynamic Acceleration Technology mode are lesser than TDP in HFM.
- 6. At Tj of 105 °C
- 7. At Tj of 50 °C
- 8. At T_j of 35 $^{\circ}$ C

Table 26. Power Specifications for the Single-Core Ultra-Low-Voltage (5.5 W) SFF Processors

- 1. The TDP specification should be used to design the processor thermal solution. The TDP is not the maximum theoretical power the processor can generate.
- 2. Not 100% tested. These power specifications are determined by characterization of the processor currents at higher temperatures and extrapolating the values for the temperature indicated.
- 3. As measured by the activation of the on-die Intel Thermal Monitor. The Intel Thermal Monitor's automatic mode is used to indicate that the maximum T_j has been reached.
- 4. The Intel Thermal Monitor automatic mode must be enabled for the processor to operate within specifications.
- 5. Processor TDP requirements in Intel Dynamic Acceleration Technology mode are lesser than TDP in HFM.
- 6. At Tj of 100° C
7. At Tj of 50° C
- At Tj of 50 °C
- 8. At Tj of 35 °C

5.1 Monitoring Die Temperature

The processor incorporates three methods of monitoring die temperature:

- Thermal Diode
- Intel*®* Thermal Monitor
- Digital Thermal Sensor

5.1.1 Thermal Diode

Intel's processors utilize an SMBus thermal sensor to read back the voltage/current characteristics of a substrate PNP transistor. Since these characteristics are a function of temperature, these parameters can be used to calculate silicon temperature values. For older silicon process technologies, it is possible to simplify the voltage/current and temperature relationships by treating the substrate transistor as though it were a simple diffusion diode. In this case, the assumption is that the beta of the transistor does not impact the calculated temperature values. The resultant "diode" model essentially predicts a quasi linear relationship between the base/emitter voltage differential of the PNP transistor and the applied temperature (one of the proportionality constants in this relationship is processor specific, and is known as the diode ideality factor). Realization of this relationship is accomplished with the SMBus thermal sensor that is connected to the transistor.

The processor, however, is built on Intel's advanced 45-nm processor technology. Due to this new processor technology, it is no longer possible to model the substrate transistor as a simple diode. To accurately calculate silicon temperature use a full bipolar junction transistor-type model. In this model, the voltage/current and temperature characteristics include an additional process dependant parameter which is known as the transistor "beta". System designers should be aware that the current thermal sensors may not be configured to account for "beta" and should work with their SMB thermal sensor vendors to ensure they have a part capable of reading the thermal diode in BJT model.

Offset between the thermal diode-based temperature reading and the Intel Thermal Monitor reading may be characterized using the Intel Thermal Monitor's Automatic mode activation of the thermal control circuit. This temperature offset must be considered when using the processor thermal diode to implement power management events. This offset is different than the diode Toffset value programmed into the processor Model-Specific Register (MSR).

[Table 27](#page-107-0) and [Table 28](#page-108-0) provide the diode interface and transistor model specifications.

Table 27. Thermal Diode Interface

Table 28. Thermal Diode Parameters Using Transistor Model

NOTES:

1. Intel does not support or recommend operation of the thermal diode under reverse bias.

2. Characterized across a temperature range of 50-105°C.

3. Not 100% tested. Specified by design characterization.

4. The ideality factor, nQ, represents the deviation from ideal transistor model behavior as exemplified by the equation for the collector current:

$$
I_C = I_S * (e^{qV}BE^{/n}Q^{kT} - 1)
$$

where I_S = saturation current, q = electronic charge, V_{BE} = voltage across the transistor base based vistor q temperature (Kelvin).

5.1.2 Intel® Thermal Monitor

The Intel Thermal Monitor helps control the processor temperature by activating the TCC (Thermal Control Circuit) when the processor silicon reaches its maximum operating temperature. The temperature at which the Intel Thermal Monitor activates the TCC is not user configurable. Bus traffic is snooped in the normal manner and interrupt requests are latched (and serviced during the time that the clocks are on) while the TCC is active.

With a properly designed and characterized thermal solution, the TCC would only be activated for very short periods of time when running the most power-intensive applications. The processor performance impact due to these brief periods of TCC activation is expected to be minor and hence not detectable. An under-designed thermal solution that is not able to prevent excessive activation of the TCC in the anticipated ambient environment may cause a noticeable performance loss and may affect the long-term reliability of the processor. In addition, a thermal solution that is significantly under designed may not be capable of cooling the processor even when the TCC is active continuously.

The Intel Thermal Monitor controls the processor temperature by modulating (starting and stopping) the processor core clocks or by initiating an Enhanced Intel SpeedStep Technology transition when the processor silicon reaches its maximum operating temperature. The Intel Thermal Monitor uses two modes to activate the TCC: automatic mode and on-demand mode. If both modes are activated, automatic mode takes precedence.

There are two automatic modes called Intel Thermal Monitor 1 (TM1) and Intel Thermal Monitor 2 (TM2). These modes are selected by writing values to the MSRs of the processor. After automatic mode is enabled, the TCC will activate only when the internal die temperature reaches the maximum allowed value for operation.

When TM1 is enabled and a high temperature situation exists, the clocks will be modulated by alternately turning the clocks off and on at a 50% duty cycle. Cycle times are processor speed-dependent and will decrease linearly as processor core frequencies increase. Once the temperature has returned to a non-critical level, modulation ceases and TCC goes inactive. A small amount of hysteresis has been included to prevent rapid

active/inactive transitions of the TCC when the processor temperature is near the trip point. The duty cycle is factory configured and cannot be modified. Also, automatic mode does not require any additional hardware, software drivers, or interrupt handling routines. Processor performance will be decreased by the same amount as the duty cycle when the TCC is active.

When TM2 is enabled and a high temperature situation exists, the processor will perform an Enhanced Intel SpeedStep Technology transition to the LFM. When the processor temperature drops below the critical level, the processor will make an Enhanced Intel SpeedStep Technology transition to the last requested operating point. The processor also supports Enhanced Multi-Threaded Thermal Monitoring (EMTTM). EMTTM is a processor feature that enhances TM2 with a processor throttling algorithm known as Adaptive TM2. Adaptive TM2 transitions to intermediate operating points, rather than directly to the LFM, once the processor has reached its thermal limit and subsequently searches for the highest possible operating point. Please ensure this feature is enabled and supported in the BIOS. Also with EMTTM enabled, the operating system can request the processor to **throttling to any point between Intel Dynamic Acceleration Technology frequency and SuperLFM frequency as long as these features are enabled in the BIOS and supported by the processor.**

The Intel Thermal Monitor automatic mode and Enhanced Multi-Threaded Thermal Monitoring must be enabled through BIOS for the processor to be operating within specifications. Intel recommends TM1 and TM2 be enabled on the processors.

TM1, TM2 and EMTTM features are collectively referred to as Adaptive Thermal Monitoring features.

TM1 and TM2 can co-exist within the processor. If both TM1 and TM2 bits are enabled in the auto-throttle MSR, TM2 takes precedence over TM1. However, if Force TM1 over TM2 is enabled in MSRs via BIOS and TM2 is not sufficient to cool the processor below the maximum operating temperature, then TM1 will also activate to help cool down the processor.

If a processor load-based Enhanced Intel SpeedStep Technology transition (through MSR write) is initiated when a TM2 period is active, there are two possible results:

- 1. If the processor load-based Enhanced Intel SpeedStep Technology transition target frequency is **higher** than the TM2 transition-based target frequency, the processor load-based transition will be deferred until the TM2 event has been completed.
- 2. If the processor load-based Enhanced Intel SpeedStep Technology transition target frequency is **lower** than the TM2 transition-based target frequency, the processor will transition to the processor load-based Enhanced Intel SpeedStep Technology target frequency point.

The TCC may also be activated via on-demand mode. If bit 4 of the ACPI Intel Thermal Monitor control register is written to a 1, the TCC will be activated immediately independent of the processor temperature. When using on-demand mode to activate the TCC, the duty cycle of the clock modulation is programmable via bits 3:1 of the same ACPI Intel Thermal Monitor control register. In automatic mode, the duty cycle is fixed at 50% on, 50% off, however in on-demand mode, the duty cycle can be programmed from 12.5% on/ 87.5% off, to 87.5% on/12.5% off in 12.5% increments. On-demand mode may be used at the same time automatic mode is enabled, however, if the system tries to enable the TCC via on-demand mode at the same time automatic mode is enabled and a high temperature condition exists, automatic mode will take precedence.

An external signal, PROCHOT# (processor hot) is asserted when the processor detects that its temperature is above the thermal trip point. Bus snooping and interrupt latching are also active while the TCC is active.

Besides the thermal sensor and thermal control circuit, the Intel Thermal Monitor also includes one ACPI register, one performance counter register, three MSR, and one I/O pin (PROCHOT#). All are available to monitor and control the state of the Intel Thermal Monitor feature. The Intel Thermal Monitor can be configured to generate an interrupt upon the assertion or deassertion of PROCHOT#.

PROCHOT# will not be asserted when the processor is in the Stop Grant, Sleep, Deep Sleep, and Deeper Sleep low-power states, hence the thermal diode reading must be used as a safeguard to maintain the processor junction temperature within maximum specification. If the platform thermal solution is not able to maintain the processor junction temperature within the maximum specification, the system must initiate an orderly shutdown to prevent damage. If the processor enters one of the above low-power states with PROCHOT# already asserted, PROCHOT# will remain asserted until the processor exits the low-power state and the processor junction temperature drops below the thermal trip point. However, PROCHOT# will de-assert for the duration of Deep Power Down Technology state (C6) residency.

If Thermal Monitor automatic mode is disabled, the processor will be operating out of specification. Regardless of enabling the automatic or on-demand modes, in the event of a catastrophic cooling failure, the processor will automatically shut down when the silicon has reached a temperature of approximately 125 \degree C. At this point the THERMTRIP# signal will go active. THERMTRIP# activation is independent of processor activity and does not generate any bus cycles. When THERMTRIP# is asserted, the processor core voltage must be shut down within the time specified in [Chapter 3](#page-24-0).

In all cases the Intel Thermal Monitor feature must be enabled for the processor to remain within specification.

5.1.3 Digital Thermal Sensor

The processor also contains an on-die Digital Thermal Sensor (DTS) that can be read via an MSR (no I/O interface). Each core of the processor will have a unique digital thermal sensor whose temperature is accessible via the processor MSRs. The DTS is the preferred method of reading the processor die temperature since it can be located much closer to the hottest portions of the die and can thus more accurately track the die temperature and potential activation of processor core clock modulation via the Thermal Monitor. The DTS is only valid while the processor is in the normal operating state (the Normal package level low-power state).

Unlike traditional thermal devices, the DTS outputs a temperature relative to the maximum supported operating temperature of the processor $(T_{J,max})$. It is the responsibility of software to convert the relative temperature to an absolute temperature. The temperature returned by the DTS will always be at or below $T_{J,max}$. Catastrophic temperature conditions are detectable via an Out Of Specification status bit. This bit is also part of the DTS MSR. When this bit is set, the processor is operating out of specification and immediate shutdown of the system should occur. The processor operation and code execution is not ensured once the activation of the Out of Specification status bit is set.

The DTS-relative temperature readout corresponds to the Thermal Monitor (TM1/TM2) trigger point. When the DTS indicates maximum processor core temperature has been reached, the TM1 or TM2 hardware thermal control mechanism will activate. The DTS and TM1/TM2 temperature may not correspond to the thermal diode reading since the thermal diode is located in a separate portion of the die and thermal gradient between the individual core DTS. Additionally, the thermal gradient from DTS to thermal diode can vary substantially due to changes in processor power, mechanical and thermal attach, and software application. The system designer is required to use the DTS to ensure proper operation of the processor within its temperature operating specifications.

Changes to the temperature can be detected via two programmable thresholds located in the processor MSRs. These thresholds have the capability of generating interrupts via the core's local APIC. Refer to the *Intel® 64 and IA-32 Architectures Software Developer's Manuals* for specific register and programming details.

5.2 Out of Specification Detection

Overheat detection is performed by monitoring the processor temperature and temperature gradient. This feature is intended for graceful shutdown before the THERMTRIP# is activated. If the processor's TM1 or TM2 are triggered and the temperature remains high, an Out Of Spec status and sticky bit are latched in the status MSR register and generates a thermal interrupt.

5.3 PROCHOT# Signal Pin

An external signal, PROCHOT# (processor hot), is asserted when the processor die temperature has reached its maximum operating temperature. If TM1 or TM2 is enabled, then the TCC will be active when PROCHOT# is asserted. The processor can be configured to generate an interrupt upon the assertion or deassertion of PROCHOT#. Refer to the an interrupt upon the assertion or deassertion of PROCHOT#. Refer to the *Intel® 64 and IA-32 Architectures Software Developer's Manuals* for specific register and programming details.

The processor implements a bi-directional PROCHOT# capability to allow system designs to protect various components from overheating situations. The PROCHOT# signal is bi-directional in that it can either signal when the processor has reached its maximum operating temperature or be driven from an external source to activate the TCC. The ability to activate the TCC via PROCHOT# can provide a means for thermal protection of system components.

Only a single PROCHOT# pin exists at a package level of the processor. When either core's thermal sensor trips, PROCHOT# signal will be driven by the processor package. If only TM1 is enabled, PROCHOT# will be asserted regardless of which core is above its TCC temperature trip point, and both cores will have their core clocks modulated. If TM2 is enabled then, regardless of which core(s) are above the TCC temperature trip point, both cores will enter the lowest programmed TM2 performance state. It is important to note that Intel recommends both TM1 and TM2 to be enabled.

When PROCHOT# is driven by an external agent, if only TM1 is enabled on both cores, then both processor cores will have their core clocks modulated. If TM2 is enabled on both cores, then both processor cores will enter the lowest programmed TM2 performance state. It should be noted that Force TM1 on TM2, enabled via BIOS, does not have any effect on external PROCHOT#. If PROCHOT# is driven by an external agent when TM1, TM2, and Force TM1 on TM2 are all enabled, then the processor will still apply only TM2.

PROCHOT# may be used for thermal protection of voltage regulators (VR). System designers can create a circuit to monitor the VR temperature and activate the TCC when the temperature limit of the VR is reached. By asserting PROCHOT# (pulled-low) and activating the TCC, the VR will cool down as a result of reduced processor power consumption. Bi-directional PROCHOT# can allow VR thermal designs to target maximum sustained current instead of maximum current. Systems should still provide proper cooling for the VR and rely on bi-directional PROCHOT# only as a backup in case of system cooling failure. The system thermal design should allow the power delivery circuitry to operate within its temperature specification even while the processor is operating at its TDP. With a properly designed and characterized thermal solution, it is anticipated that bi-directional PROCHOT# would only be asserted for very short periods

of time when running the most power-intensive applications. An under-designed thermal solution that is not able to prevent excessive assertion of PROCHOT# in the anticipated ambient environment may cause a noticeable performance loss.

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